

# 2SC5609G

## Silicon NPN epitaxial planar type

For general amplification

Complementary to 2SA2021G

### ■ Features

- High forward current transfer ratio  $h_{FE}$

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
Collector current	$I_C$	100	mA
Peak collector current	$I_{CP}$	200	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

### ■ Package

- Code  
SSSMini3-F2
- Pin Name
  1. Base
  2. Emitter
  3. Collector

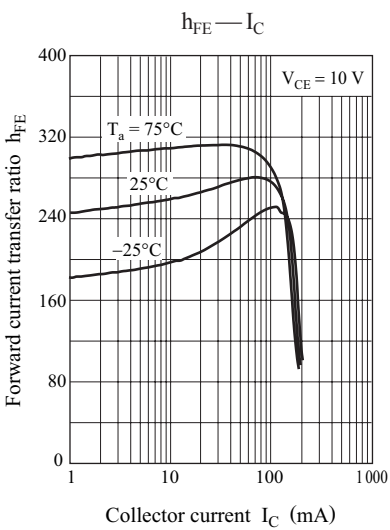
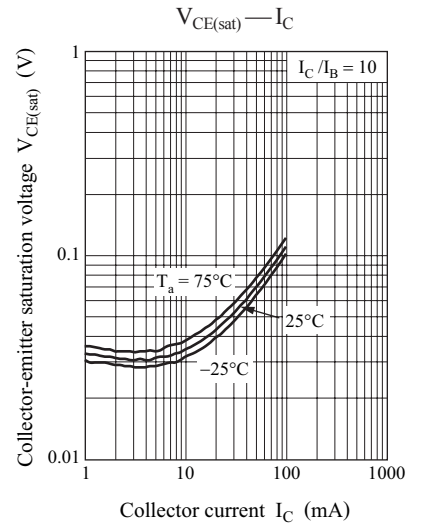
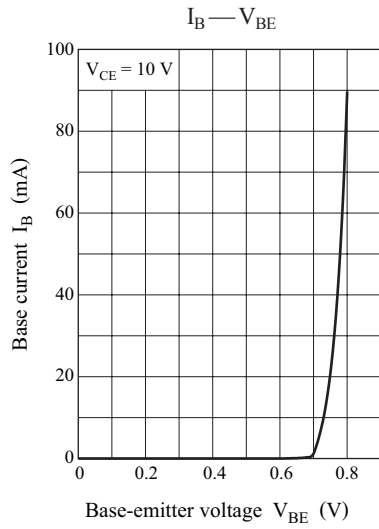
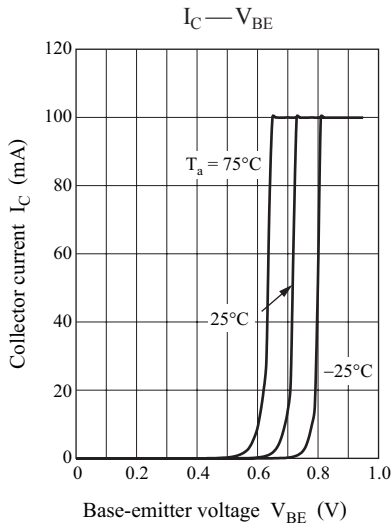
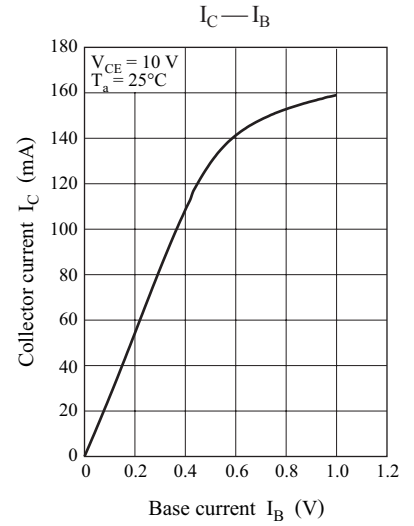
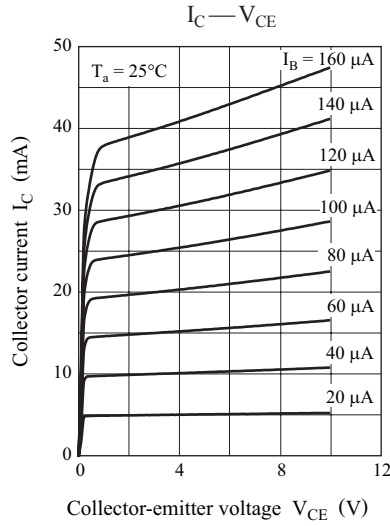
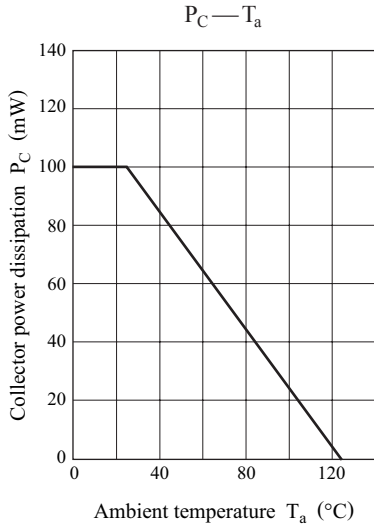
### ■ Marking Symbol: 3F

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	60			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 10 \text{ V}, I_B = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	180		390	—
	$h_{FE2}^*$	$V_{CE} = 2 \text{ V}, I_C = 100 \text{ mA}$	90			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.1	0.3	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance (Common base, input open circuited)	$C_{re}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5		pF

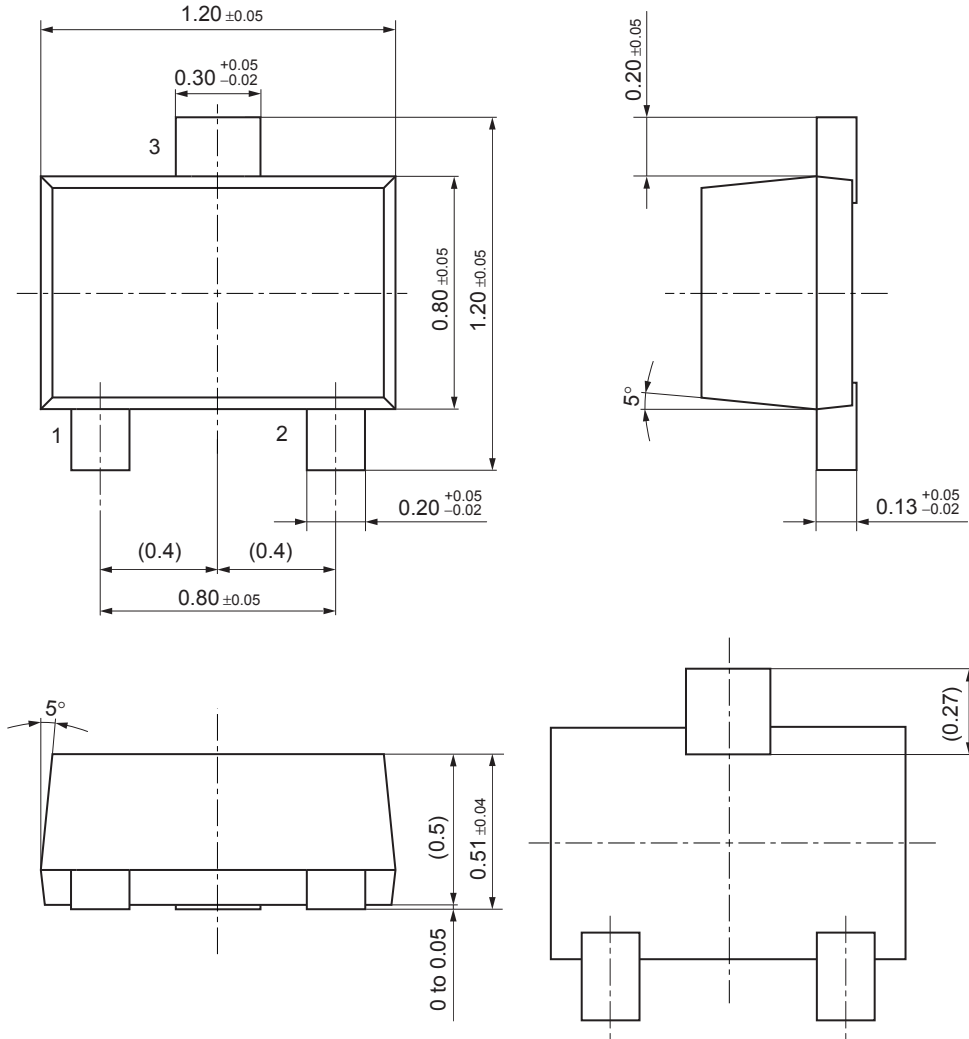
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Pulse measurement



SSSMini3-F2

Unit: mm



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